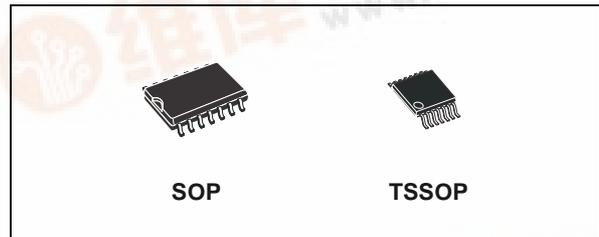




74VHCT03A

QUAD 2-INPUT OPEN DRAIN NAND GATE

- HIGH SPEED: $t_{PZ} = 3.9 \text{ ns}$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS:
 $V_{IH} = 2V$ (MIN.), $V_{IL} = 0.8V$ (MAX)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPR)} = 4.5V$ to $5.5V$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 03
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: $V_{OLP} = 0.8V$ (MAX.)



ORDER CODES

PACKAGE	TUBE	T & R
SOP	74VHCT03AM	74VHCT03AMTR
TSSOP		74VHCT03ATTR

DESCRIPTION

The 74VHCT03A is an advanced high-speed CMOS QUAD 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provides high noise immunity and stable output.

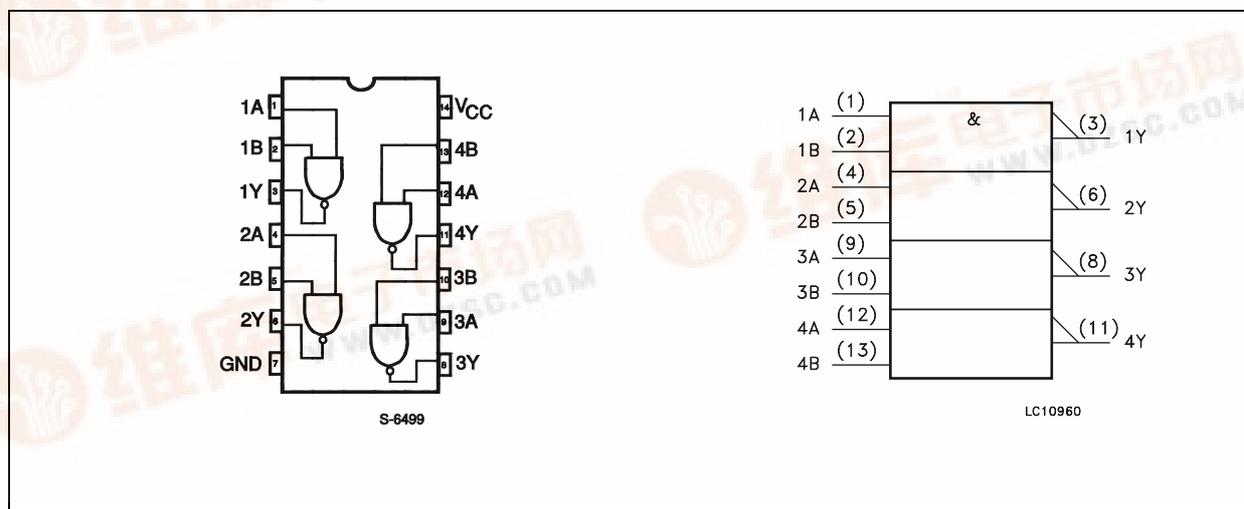
This device can, with an external pull-up resistor, be used in wired AND configuration. This device can also be used as a led driver and in any other application requiring a current sink.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no

regard to the supply voltage. This device can be used to interface 5V to 3V since all inputs are equipped with TTL threshold.

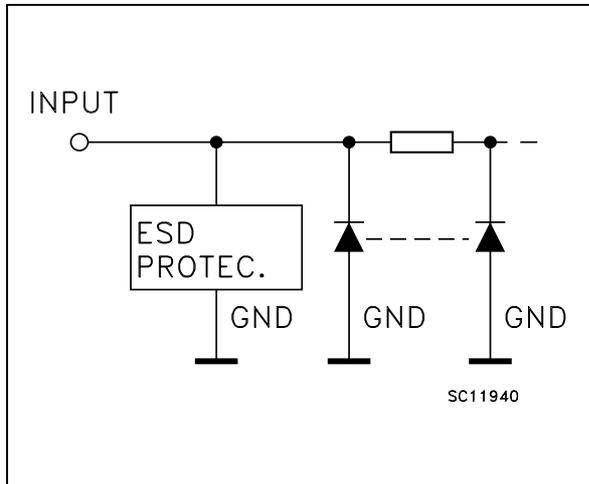
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



74VHCT03A

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (see note 3) (V _{CC} = 5.0 ± 0.5V)	0 to 20	ns/V

1) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OL}	Low Level Output Voltage	4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =8 mA			0.36		0.44		0.44	
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = 0V to 5.5V			±0.25		± 2.5		± 2.5	μA
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1.0		± 1.0	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			2		20		20	μA
Δ I _{CC}	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V _{CC} or GND			1.35		1.5		1.5	mA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition			Value						Unit	
		V _{CC} (*) (V)	C _L (pF)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PZL}	Propagation Delay Time	5.0	15		3.9	5.1	1.0	6.0	1.0	6.0	ns	
		5.0	50		4.4	5.7	1.0	6.6	1.0	6.6		
t _{PLZ}	Propagation Delay Time	5.0	50		7.5	9.8	1.0	11.3	1.0	11.3	ns	

(*) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
				T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance				5.8	10		10		10	pF
C _{OUT}	Output Capacitance				8.8						pF
C _{PD}	Power Dissipation Capacitance (note 1)				6						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} × V_{CC} × f_{IN} + I_{CC}/4 (per gate)

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DYNAMIC SWITCHING CHARACTERISTICS

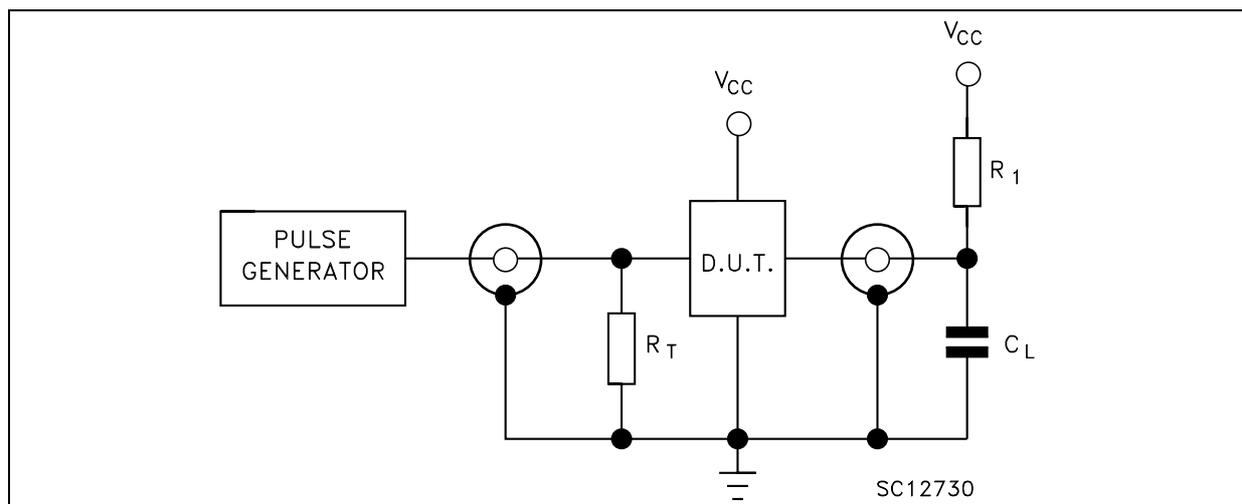
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C _L = 50 pF		0.3	0.8					V
V _{OLV}				-0.8	-0.3						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		2.0							
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				0.8					

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.0V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.0V. Inputs under test switching: 3.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

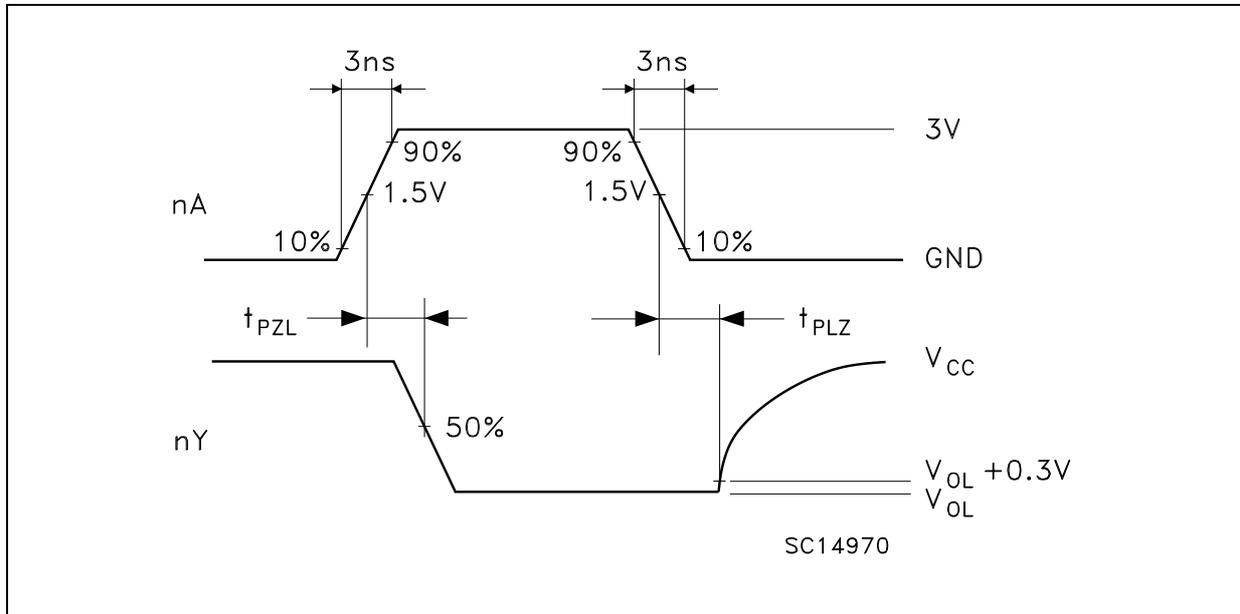
TEST CIRCUIT



C_L = 15/50pF or equivalent (includes jig and probe capacitance)

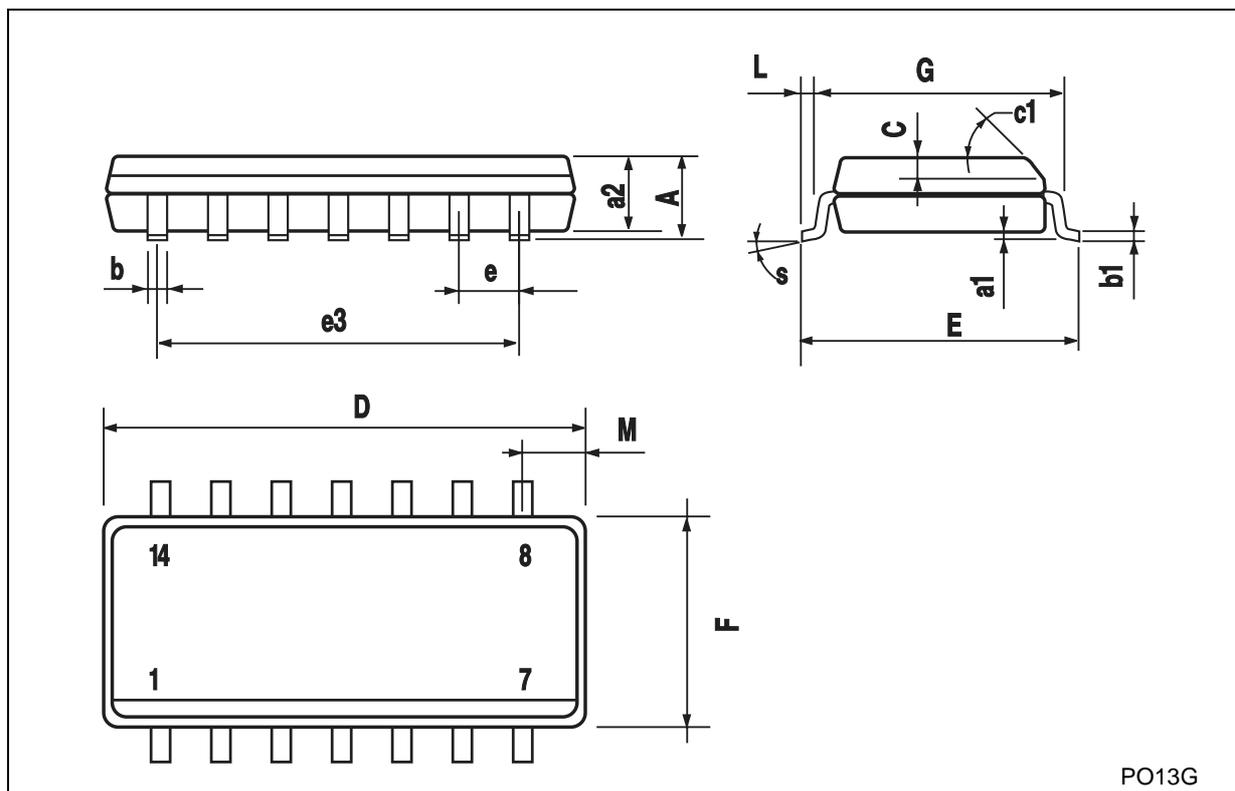
R_L = R₁ = 1KΩ or equivalent

R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

SO-14 MECHANICAL DATA

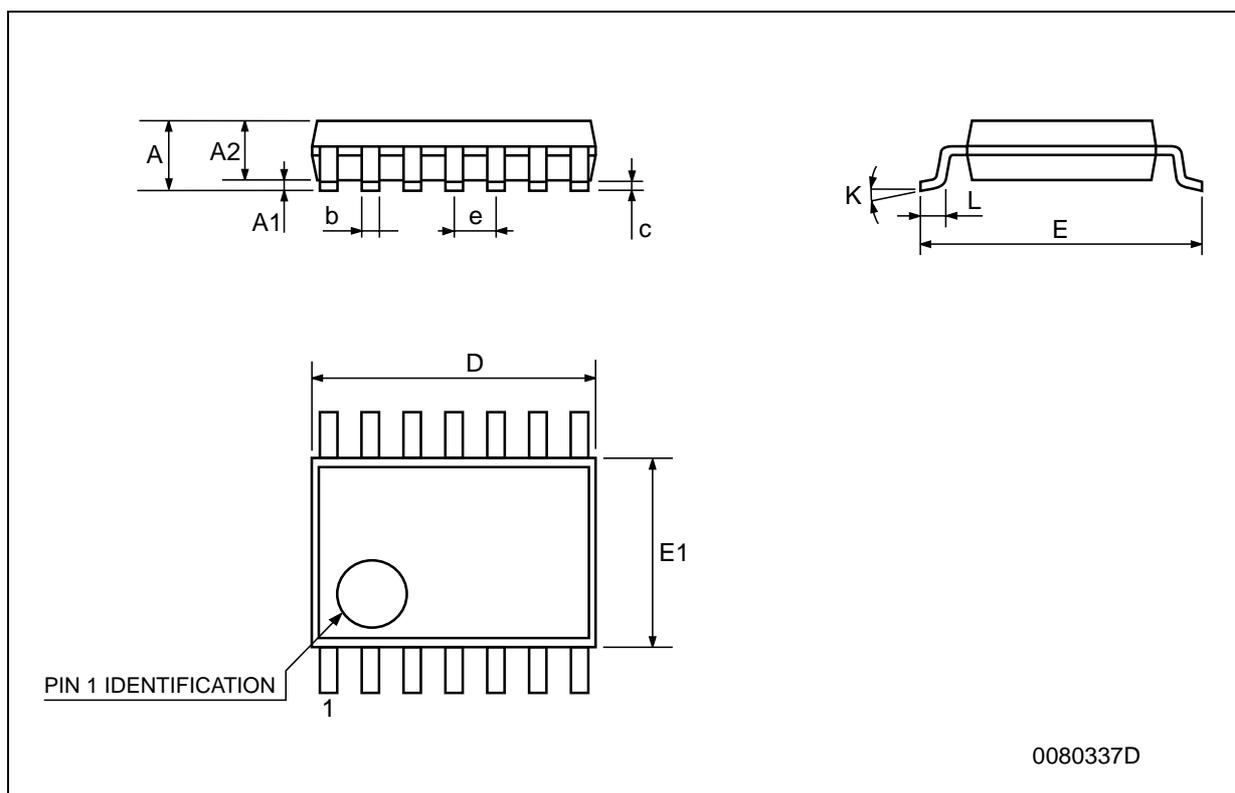
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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